

## Silicon Standard Recovery Diode

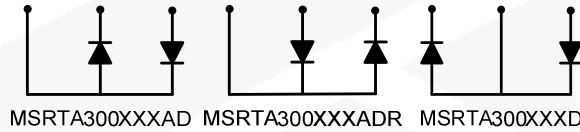
$V_{RRM} = 1200\text{ V} - 1600\text{ V}$

$I_{F(AV)} = 300\text{ A}$

### Features

- High Surge Capability
- Types from 1200 V to 1600 V  $V_{RRM}$
- Isolation Type Package
- Electrically Isolated Base Plate
- Not ESD Sensitive

Heavy Three Tower Package



### Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	MSRTA300120(A)D	MSRTA300140(A)D	MSRTA300160(A)D	Unit
Repetitive peak reverse voltage	$V_{RRM}$		1200	1400	1600	V
DC blocking voltage	$V_{DC}$		1200	1400	1600	V
Operating temperature	$T_j$		-55 to 150	-55 to 150	-55 to 150	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-55 to 150	-55 to 150	-55 to 150	$^\circ\text{C}$

### Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	MSRTA300120(A)D	MSRTA300140(A)D	MSRTA300160(A)D	Unit
Average forward current (per leg)	$I_{F(AV)}$	$T_C = 125\text{ }^\circ\text{C}$	300	300	300	A
Peak forward surge current (per leg)	$I_{FSM}$	$t_p = 8.3\text{ ms}$ , half sine	3800	3800	3800	A
Maximum instantaneous forward voltage (per leg)	$V_F$	$I_{FM} = 300\text{ A}$ , $T_j = 25\text{ }^\circ\text{C}$	1.1	1.1	1.1	V
Maximum instantaneous reverse current at rated DC blocking voltage (per leg)	$I_R$	$T_j = 25\text{ }^\circ\text{C}$	20	20	20	$\mu\text{A}$
		$T_j = 150\text{ }^\circ\text{C}$	10	10	10	mA

### Thermal characteristics

Maximum thermal resistance, junction - case (per leg)	$R_{\theta jc}$		0.28	0.28	0.28	$^\circ\text{C/W}$
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Figure .1- Typical Forward Characteristics

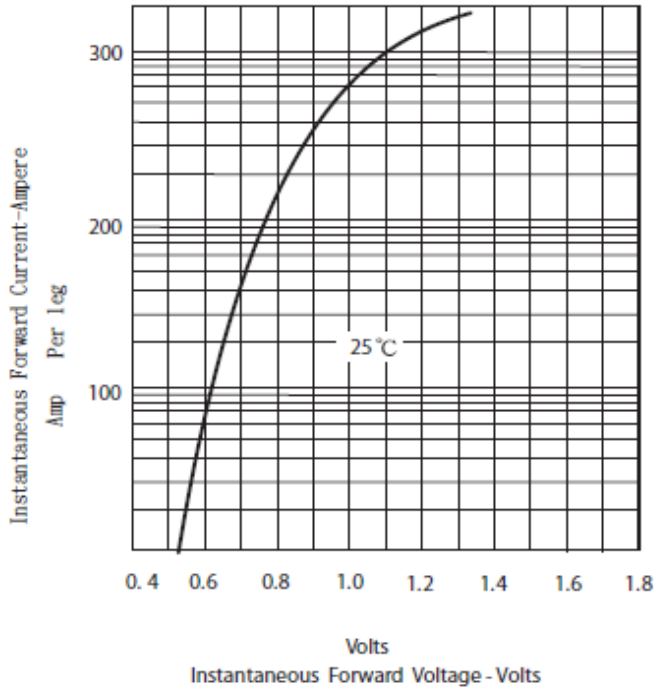


Figure.2 Forward Derating Curve

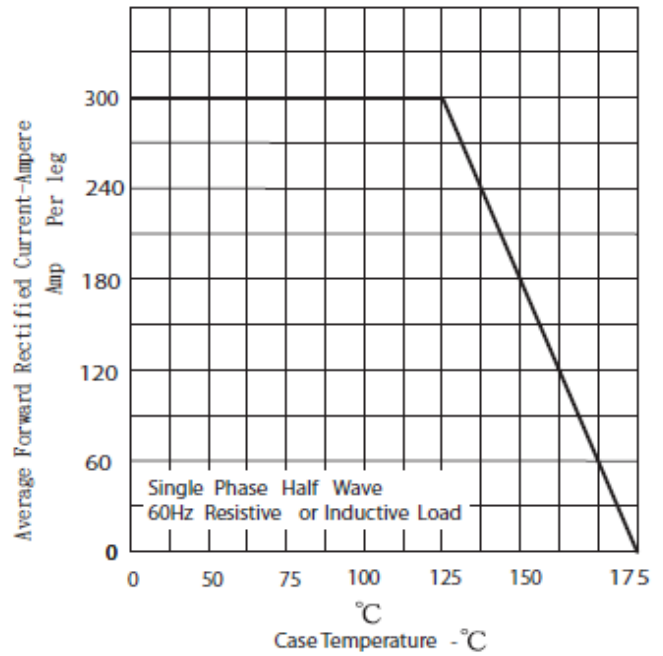


Figure.3-Peak Forward Surge Current

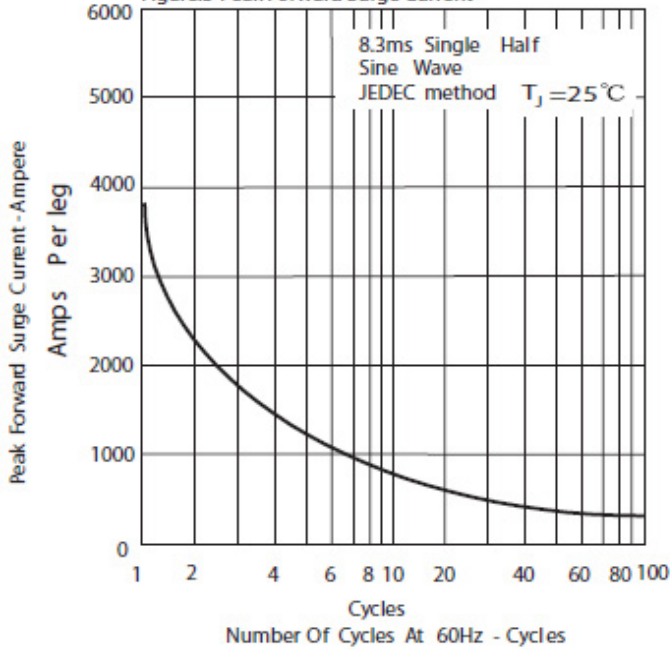
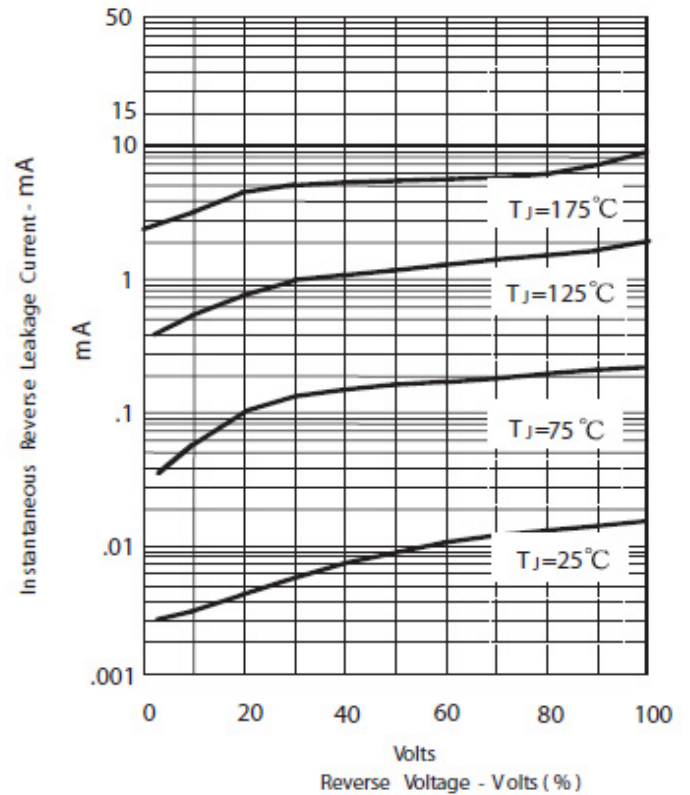
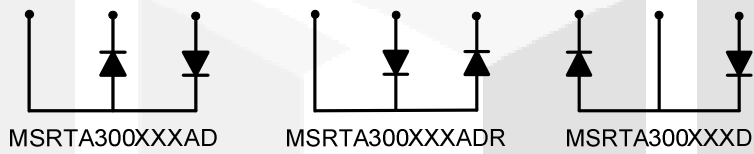
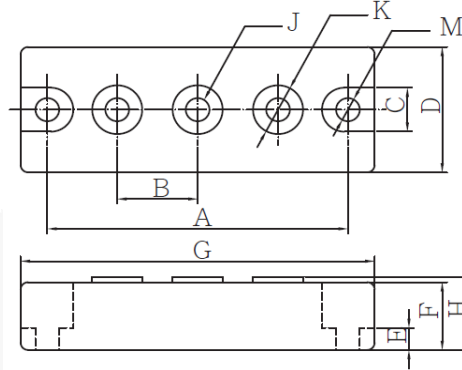


Figure .4 -Typical Reverse Characteristics



## Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	3.150	NOM	80.01	NOM	
B	.872	.892	22.15	22.65	
C	.465	.479	11.82	12.18	
D	1.337	1.356	33.95	34.45	
E	.230	.234	5.84	6.16	
F	.725	REF	18.42	REF	
G	3.668	3.768	93.17	95.71	
H	---	.791	---	20.10	
J	1/4-20 UNC FULL				
K	.509	.538	12.92	13.68	∅
M	.238	.258	6.05	6.55	∅

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